

TSM680P06D

Taiwan Semiconductor

Dual P-Channel MOSFET

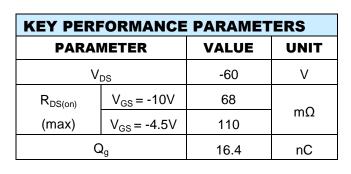
-60V, -12A, $68m\Omega$

FEATURES

- Fast switching
- Low thermal resistance package
- Low profile package
- Pb-free plating
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

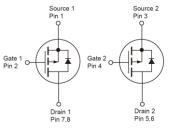
APPLICATION

- Power Supply
- Motor Control









Dual P-Channel MOSFET

Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

| ABSOLUTE MAXIMUM RATIN | IGS (T _A = 25°C unl | ess otherwise note | ed) | |
|--|----------------------------------|-----------------------------------|--------------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | | V _{DS} | -60 | V |
| Gate-Source Voltage | | V _{GS} | ±20 | V |
| Continuous Drain Current (Note 1) | $T_{\rm C} = 25^{\circ}{\rm C}$ | - I _D | -12 | ٨ |
| Continuous Drain Current | $T_{\rm C} = 100^{\circ}{\rm C}$ | | -8 | A |
| Pulsed Drain Current (Note 2) | | I _{DM} | -48 | А |
| Total Power Dissipation @ $T_c = 25^{\circ}C$ | | P _{DTOT} | 3.5 | W |
| Single Pulsed Avalanche Energy (Note 3) | | E _{AS} | 7.2 | mJ |
| Single Pulsed Avalanche Current (Note 3) | | I _{AS} | 12 | А |
| Operating Junction and Storage Temperature Range | | T _J , T _{STG} | - 55 to +150 | °C |

| THERMAL PERFORMANCE | | | |
|--|------------------|-------|------|
| PARAMETER | SYMBOL | LIMIT | UNIT |
| Junction to Case Thermal Resistance | R _{eJC} | 4.5 | °C/W |
| Junction to Ambient Thermal Resistance | R _{eja} | 85 | °C/W |

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air

TSM680P06D



Taiwan Semiconductor

| PARAMETER | CONDITIONS | SYMBOL | MIN | ТҮР | MAX | UNIT |
|--|--|------------------------|------|------|------|------|
| Static (Note 4) | | | | | | • |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_{D} = -250\mu A$ | BV _{DSS} | -60 | | | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | V _{GS(TH)} | -1.2 | -1.6 | -2.5 | V |
| Gate Body Leakage | $V_{GS} = \pm 20V, V_{DS} = 0V$ | I _{GSS} | | | ±100 | nA |
| Zero Gate Voltage Drain Current | $V_{DS} = -60V, V_{GS} = 0V$ | I _{DSS} | | | -1 | μA |
| | V _{DS} = -48V, Tc = 125°C | | | | -10 | |
| | $V_{GS} = -10V, I_{D} = -6A$ | | | 54 | 68 | mΩ |
| Drain-Source On-State Resistance | $V_{GS} = -4.5V, I_D = -3A$ | $R_{DS(on)}$ | | 90 | 110 | |
| Forward Transconductance | $V_{DS} = -10V, I_{D} = -6A$ | g _{fs} | | 8.5 | | S |
| Dynamic (Note 5) | | | | | | • |
| Total Gate Charge | | Qg | | 16.4 | | |
| Gate-Source Charge | $V_{DS} = -30V, I_{D} = -6A,$ | Q_{gs} | | 2.8 | | nC |
| Gate-Drain Charge | V _{GS} = -10V | Q_{gd} | | 3.6 | | |
| Input Capacitance | | C _{iss} | | 870 | | |
| Output Capacitance | $V_{DS} = -30V, V_{GS} = 0V,$ | C _{oss} | | 70 | | pF |
| Reverse Transfer Capacitance | f = 1.0MHz | C _{rss} | | 42 | | |
| Switching (Note 6) | | | • | | | |
| Turn-On Delay Time | | t _{d(on)} | | 8.3 | | |
| Turn-On Rise Time | $V_{DD} = -30V, I_D = -1A,$ $R_{GEN} = 6\Omega$ | t _r | | 42.4 | | |
| Turn-Off Delay Time | | t _{d(off)} | | 64.6 | | ns |
| Turn-Off Fall Time | | t _f | | 16.4 | | |
| Source-Drain Diode (Note 4) | | | • | | | |
| Maximum Continuous Drain-Source Diode Forward Current | Integral reverse diode in the MOSFET | I _S | | | -12 | A |
| Maximum Pulse Drain-Source Diode Forward Current | | I _{SM} | | | -48 | A |
| Diode-Source Forward Voltage | $V_{GS} = 0V, I_{S} = -1A$ | V _{SD} | | | -1 | V |

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 0.1mH, I_{AS} = -12A, V_{DD} = -25V, R_G = 25\Omega, Starting T_J = 25 ^{o}C

4. Pulse test: PW \leq 300µs, duty cycle \leq 2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



ORDERING INFORMATION (EXAMPLE)

| PART NO. | PACKAGE | PACKING |
|--------------------|-------------|--------------------|
| TSM680P06DPQ56 RLG | PDFN56 Dual | 2,500pcs / 13"Reel |

Note:

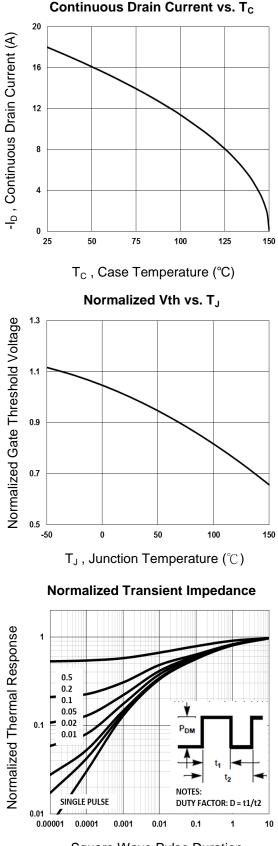
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

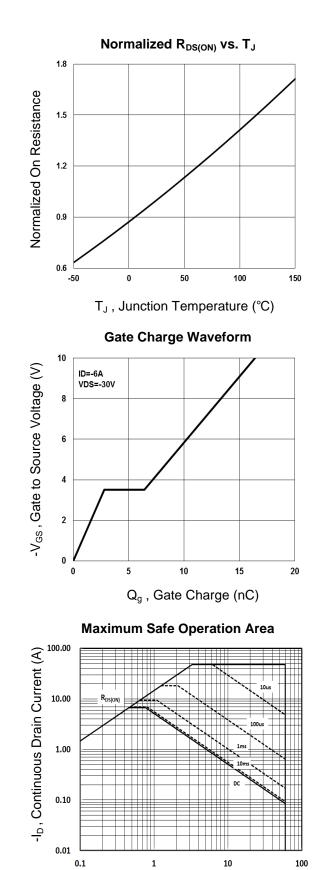


CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



Square Wave Pulse Duration



⁻V_{DS}, Drain to Source Voltage (V)

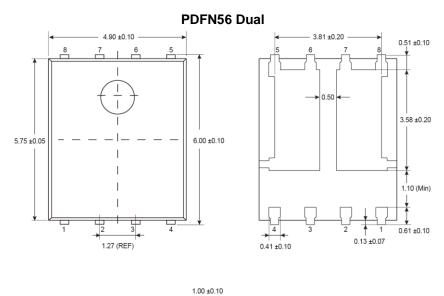




TAIWAN

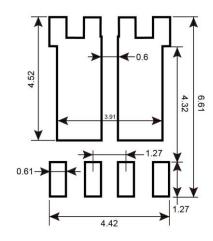
IICONDUCTOR

9





SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM

| | Y = Year CodeM = Month Code for Halogen Free Product | |
|-------------------------|---|--|
| TSC 680P6D YML | O =Jan P =Feb Q =Mar R =Apr | |
| | $\mathbf{S} = \mathbf{W}\mathbf{a}\mathbf{y}$ $\mathbf{I} = \mathbf{J}\mathbf{u}\mathbf{I}$ $\mathbf{U} = \mathbf{J}\mathbf{u}\mathbf{I}$ $\mathbf{V} = \mathbf{A}\mathbf{u}\mathbf{g}$ | |
| ** 1 | W =Sep X =Oct Y =Nov Z =Dec | |
| L = Lot Code (1~9, A~Z) | | |



TSM680P06D

Taiwan Semiconductor

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Taiwan Semiconductor manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B DMN1006UCA6-7